

# DMG20102

Silicon NPN epitaxial planar type (Tr1)  
 Silicon PNP epitaxial planar type (Tr2)

For general amplification

■ Features

- High forward current transfer ratio  $h_{FE}$  with excellent linearity
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant  
 (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: CY

■ Basic Part Number

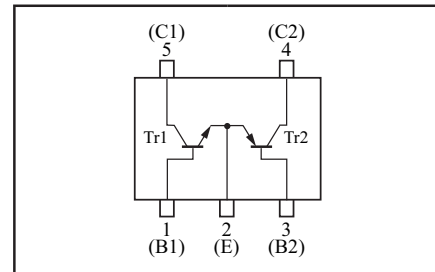
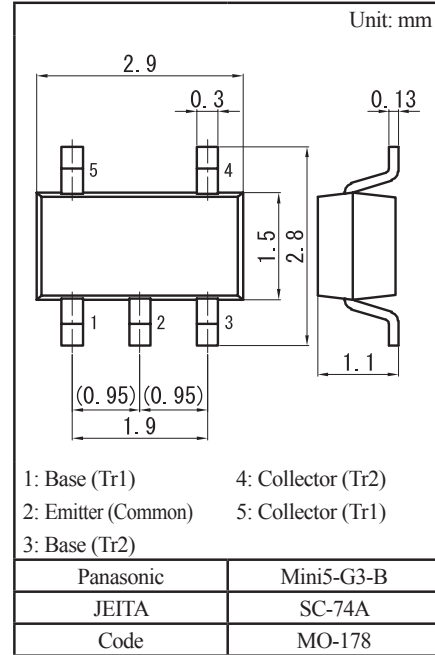
DSC2002 + DSA2002 (Common emitter)

■ Packaging

DMG201020R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
	Collector current	$I_C$	500	mA
	Peak collector current	$I_{CP}$	1	A
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-60	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
	Collector current	$I_C$	-500	mA
	Peak collector current	$I_{CP}$	-1	A
Overall	Total power dissipation	$P_T$	300	mW
	Junction temperature	$T_j$	150	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

#### • Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$	60			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = 2 \text{mA}, I_{\text{B}} = 0$	50			V
Emitter-base voltage (Collector open)	$V_{\text{EBO}}$	$I_{\text{E}} = 10 \mu\text{A}, I_{\text{C}} = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = 20 \text{V}, I_{\text{E}} = 0$			0.1	$\mu\text{A}$
Forward current transfer ratio	$h_{\text{FE1}}$	$V_{\text{CE}} = 10 \text{V}, I_{\text{C}} = 150 \text{mA}$	120		340	—
	$h_{\text{FE2}}$	$V_{\text{CE}} = 10 \text{V}, I_{\text{C}} = 500 \text{mA}$	40			—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = 300 \text{mA}, I_{\text{B}} = 30 \text{mA}$		0.1	0.6	V
Transition frequency	$f_{\text{T}}$	$V_{\text{CE}} = 10 \text{V}, I_{\text{C}} = 50 \text{mA}$		160		MHz
Collector output capacitance (Common base, input open circuited)	$C_{\text{ob}}$	$V_{\text{CB}} = 10 \text{V}, I_{\text{E}} = 0, f = 1 \text{MHz}$		4.8	15	pF

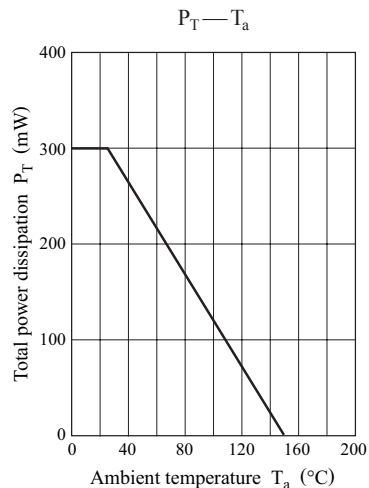
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### • Tr2

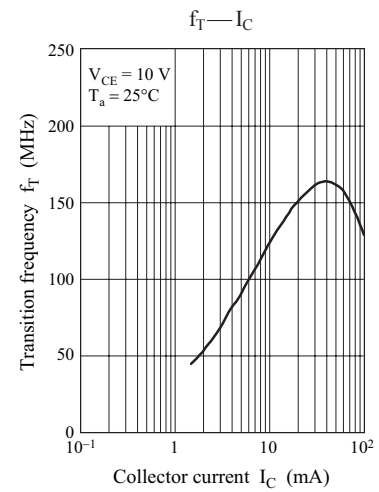
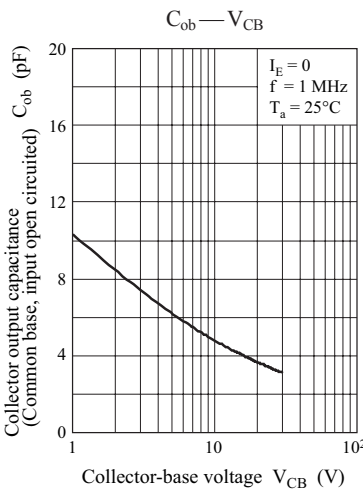
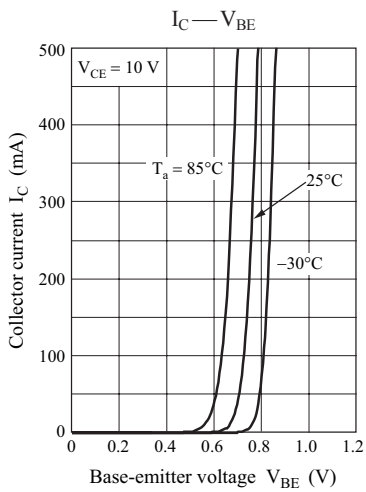
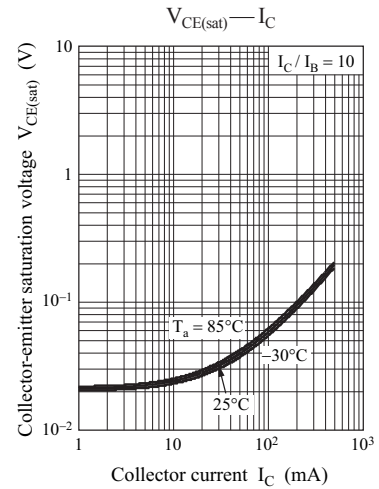
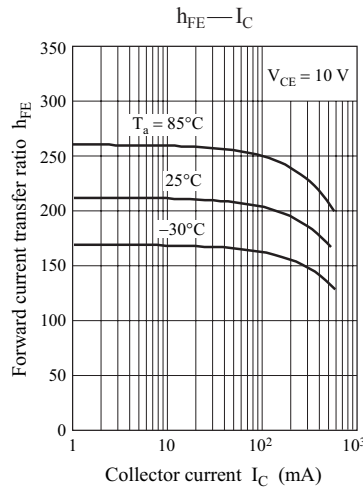
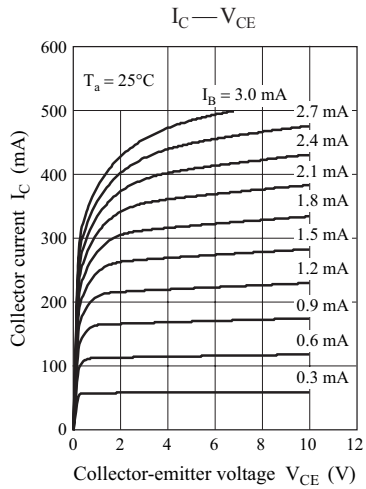
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-60			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = -2 \text{mA}, I_{\text{B}} = 0$	-50			V
Emitter-base voltage (Collector open)	$V_{\text{EBO}}$	$I_{\text{E}} = -10 \mu\text{A}, I_{\text{C}} = 0$	-5			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = -20 \text{V}, I_{\text{E}} = 0$			-0.1	$\mu\text{A}$
Forward current transfer ratio	$h_{\text{FE1}}$	$V_{\text{CE}} = -10 \text{V}, I_{\text{C}} = -150 \text{mA}$	120		340	—
	$h_{\text{FE2}}$	$V_{\text{CE}} = -10 \text{V}, I_{\text{C}} = -500 \text{mA}$	40			—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -300 \text{mA}, I_{\text{B}} = -30 \text{mA}$		-0.2	-0.6	V
Base-emitter saturation voltage	$V_{\text{BE(sat)}}$	$I_{\text{C}} = -300 \text{mA}, I_{\text{B}} = -30 \text{mA}$		-0.9	-1.5	V
Transition frequency	$f_{\text{T}}$	$V_{\text{CE}} = -10 \text{V}, I_{\text{C}} = -50 \text{mA}$		130		MHz
Collector output capacitance (Common base, input open circuited)	$C_{\text{ob}}$	$V_{\text{CB}} = -10 \text{V}, I_{\text{E}} = 0, f = 1 \text{MHz}$		7.3	15	pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

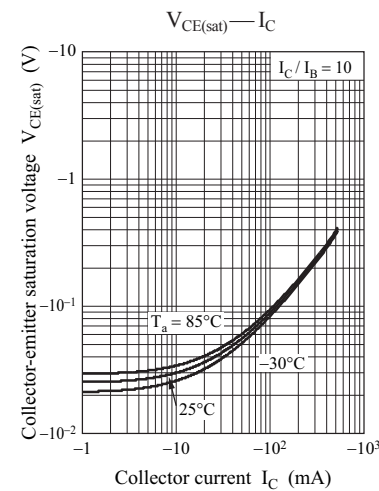
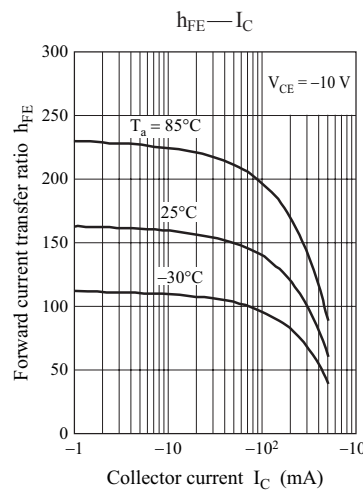
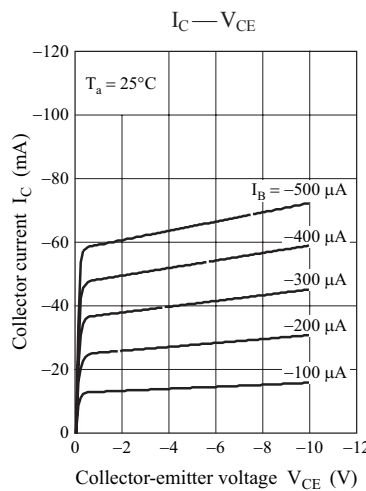
#### Common characteristics chart

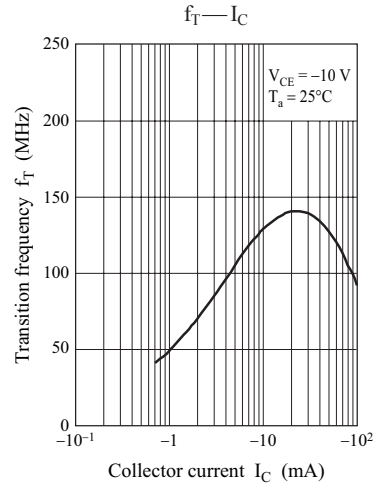
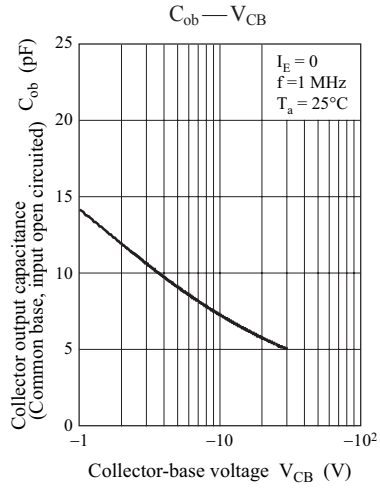
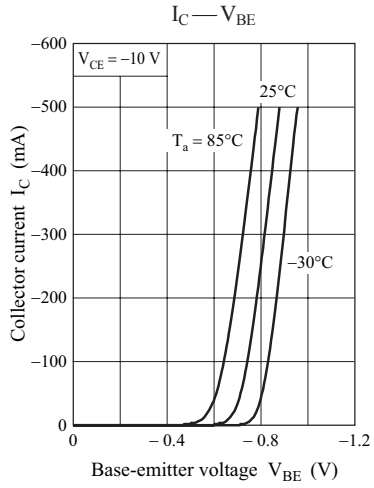


Characteristics charts of Tr1



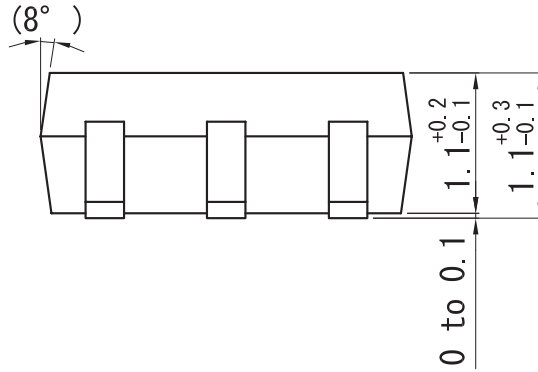
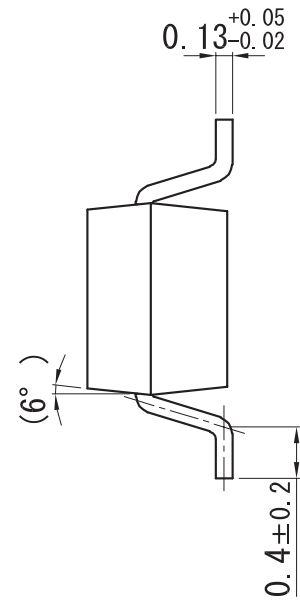
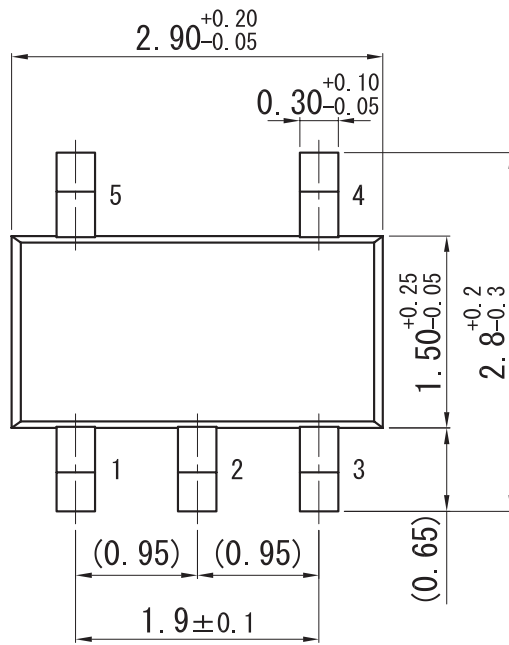
Characteristics charts of Tr2



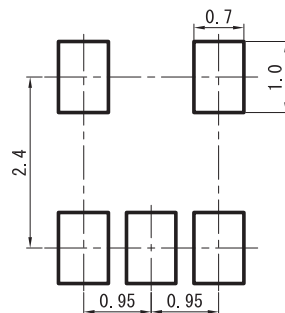


Mini5-G3-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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